

IN THE CLAIMS:

Please amend Claims 1 and 11 as follows:

1. (Twice Amended) A method for forming a semiconductor device having a laminated structure of a dielectric film made from a metal oxide which is formed on a surface of a substrate and a CVD high melting point metal nitride film directly formed thereover, wherein said metal nitride film is directly formed on said dielectric film by introducing a source gas containing said high melting point metal into a chamber in which said substrate is contained,

said method comprising a step of treating said substrate in an ambient that is non-reactive with respect to said metal oxide formed on said surface of said substrate in said chamber [with] wherein said non-reactive ambient includes at least one of a gas non-reactive with respect to said metal oxide contained in said dielectric film and NH_3 gas,

keeping said temperature of said substrate at a prescribed temperature, before said source gas containing said high melting point metal is introduced into said chamber.